<u>TOSHIBA</u>

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type

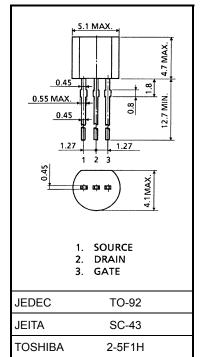
2SJ148

High Speed Switching Applications Analog Switch Applications Interface Applications

- Excellent switching time: t_{on} = 14 ns (typ.)
- High forward transfer admittance: $|\,Y_{\rm fs}\,|$ = 100 mS (min)
- Low on resistance: R_{DS} (ON) = 1.3 Ω (typ.)
- Enhancement-mode
- Complementary to 2SK982

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	-60	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC	ID	-200	mA	
	Pulse	I _{DP}	-800		
Drain power dissipation (Ta = 25°C)		PD	400	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Weight: 0.21 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of

high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratinge.

 $temperature/current/voltage, \ etc.) \ are \ within \ the \ absolute \ maximum \ ratings.$

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm

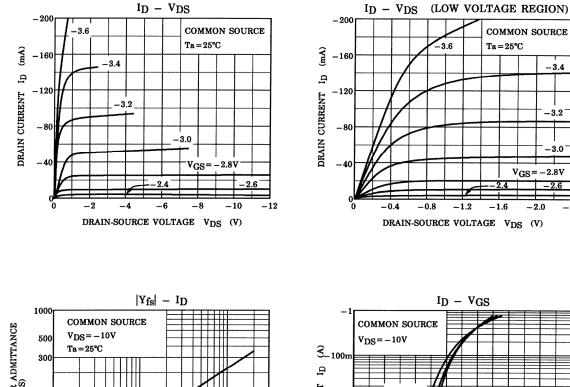
Electrical Characteristics (Ta = 25°C)

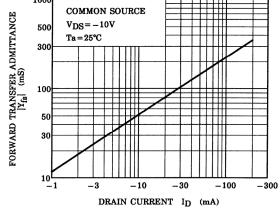
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GSS}	$V_{GS}=\pm 10~V,~V_{DS}=0$			±100	nA
Drain cut-off curre	ent	I _{DSS}	$V_{DS} = -60 \text{ V}, \text{ V}_{GS} = 0$			-10	μA
Drain-source brea	akdown voltage	V (BR) DSS	$I_D = -1 \text{ mA}, V_{GS} = 0$	-60			V
Gate threshold vo	oltage	V _{th}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA}$	-2		-3.5	V
Forward transfer	admittance	Y _{fs}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -50 \text{ mA}$	100		_	mS
Drain-source ON	resistance	R _{DS (ON)}	$I_D = -50 \text{ mA}, \text{ V}_{GS} = -10 \text{ V}$		1.3	2.0	Ω
Drain-source ON	voltage	V _{DS (ON)}	$I_D = -50 \text{ mA}, \text{ V}_{GS} = -10 \text{ V}$		-65	-100	mV
Input capacitance	;	C _{iss}	$V_{DS} = -10 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1 \text{ MHz}$		73	85	pF
Reverse transfer capacitance		C _{rss}	$V_{DS} = -10 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1 \text{ MHz}$		15	22	pF
Output capacitance		C _{oss}	$V_{DS} = -10 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1 \text{ MHz}$		48	60	pF
Switching time	Rise time	tr	$ \begin{array}{c} 0 \\ -10V \\ 10\mu s \end{array} \begin{array}{c} ID = -100mA \\ VIN \\ C \\ m^{10} \end{array} \begin{array}{c} VOUT \\ VDD = -30V \end{array} $	_	8		ns
	Turn-on time	t _{on}			14	_	
	Fall time	t _f		_	35	_	
	Turn-off Time	toff	$\label{eq:VIN:tr} \begin{split} &V_{\text{IN}}: t_{\text{f}}, t_{\text{f}} < 5 \text{ns} \\ &D.U. \leq 1\% (Z_{\text{out}} = 50 \Omega) \end{split}$		100		

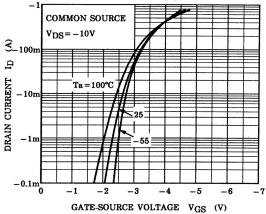
This transistor is the electrostatic sensitive device. Please handle with caution.

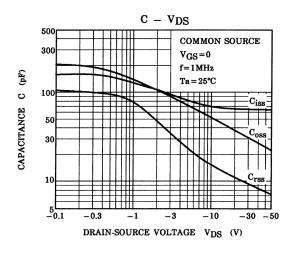
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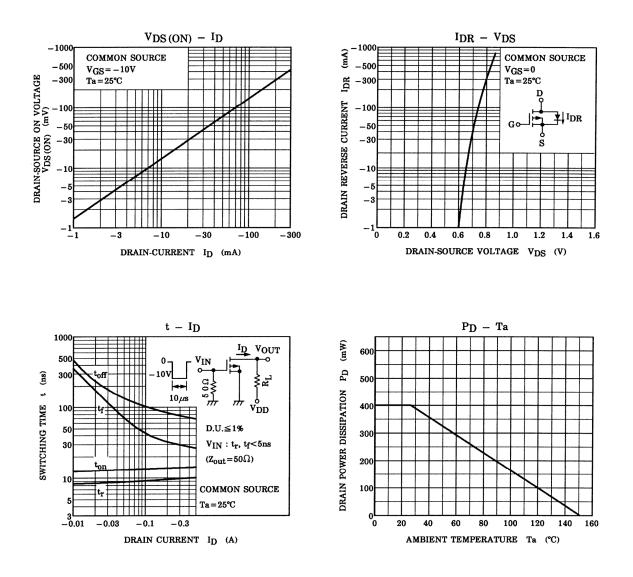








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20070701-EN GENERAL

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